HMC406MS8G / 406MS8GE

# GaAs InGaP HBT MMIC POWER AMPLIFIER, 5-6 GHz 

## Typical Applications

The HMC406MS8G(E) is ideal for:

- WiMAX \& WiLAN
- DSRC
- Military \& Maritime
- Private Mobile Radio
- UNII \& ISM

Functional Diagram


Features<br>Gain: 17 dB<br>Saturated Power: +29 dBm<br>$38 \%$ PAE<br>Supply Voltage: +5 V<br>Power Down Capability<br>Low External Part Count

## General Description

The HMC406MS8G(E) is a high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC Power amplifier which operates between 5 and 6 GHz . The amplifier is packaged in a low cost, surface mount 8 leaded package with an exposed base for improved RF and thermal performance. With a minimum of external components, the amplifier provides 17 dB of gain and +29 dBm of saturated power at $38 \%$ PAE from a +5 V supply voltage. Vpd can be used for full power down or RF output power/ current control.

Electrical Specifications, $T_{A}=+25^{\circ} \mathrm{C}$, $\mathrm{Vs}=5 \mathrm{~V}, \mathrm{Vpd}=5 \mathrm{~V}$

| Parameter |  | Min. | Typ. | Max. | Min. | Typ. | Max. | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Frequency Range |  | 5-6 |  |  | 5.7-5.9 |  |  | GHz |
| Gain |  | 13 | 16 | 21 | 14 | 17 | 21 | dB |
| Gain Variation Over Temperature |  |  | 0.03 | 0.04 |  | 0.03 | 0.04 | $\mathrm{dB} /{ }^{\circ} \mathrm{C}$ |
| Input Return Loss |  |  | 10 |  |  | 11 |  | dB |
| Output Return Loss |  |  | 8 |  |  | 9 |  | dB |
| Output Power for 1 dB Compression (P1dB) |  | 21 | 24 |  | 24 | 27 |  | dBm |
| Saturated Output Power (Psat) |  |  | 27 |  |  | 29 |  | dBm |
| Output Third Order Intercept (IP3) |  | 34 | 38 |  | 34 | 38 |  | dBm |
| Noise Figure |  |  | 6.0 |  |  | 6.0 |  | dB |
| Supply Current (Icq) | $\mathrm{Vpd}=0 \mathrm{~V} / 5 \mathrm{~V}$ |  | $0.002 / 300$ |  |  | $0.002 / 300$ |  | mA |
| Control Current (lpd) | $\mathrm{Vpd}=5 \mathrm{~V}$ |  | 7 |  |  | 7 |  | mA |
| Switching Speed | tON, tOFF |  | 35 |  |  | 35 |  | ns |

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Broadband Gain \& Return Loss


Input Return Loss vs. Temperature


P1dB vs. Temperature


## GaAs InGaP HBT MMIC POWER AMPLIFIER, 5-6 GHz

Gain vs. Temperature


Output Return Loss vs. Temperature


Psat vs. Temperature


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Power Compression @ 5.8 GHz


Noise Figure vs. Temperature


Reverse Isolation vs. Temperature


Output IP3 vs. Temperature


Gain \& Power vs. Supply Voltage


Gain, Power \& Quiescent
Supply Current vs. Vpd @ 5.8 GHz


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## GaAs InGaP HBT MMIC POWER AMPLIFIER，5－6 GHz

## Absolute Maximum Ratings

| Collector Bias Voltage（Vcc） | +5.5 V |
| :--- | :--- |
| Control Voltage（Vpd） | +5.5 V |
| RF Input Power（RFIN）（Vs＝Vpd＝＋5V） | +20 dBm |
| Junction Temperature | $150^{\circ} \mathrm{C}$ |
| Continuous Pdiss $\left(\mathrm{T}=85^{\circ} \mathrm{C}\right)$ <br> （derate $32 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $\left.85^{\circ} \mathrm{C}\right)$ | 2.1 W |
| Thermal Resistance <br> （junction to ground paddle） | $31^{\circ} \mathrm{C} / \mathrm{W}$ |
| Storage Temperature | -65 to $+150^{\circ} \mathrm{C}$ |
| Operating Temperature | -40 to $+85^{\circ} \mathrm{C}$ |

## Outline Drawing



## Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ${ }^{[3]}$ |
| :---: | :---: | :---: | :---: | :---: |
| HMC406MS8G | Low Stress Injection Molded Plastic | Sn／Pb Solder | MSL1 ${ }^{[1]}$ | H406 <br> XXXX |
| HMC406MS8GE | RoHS－compliant Low Stress Injection Molded Plastic | $100 \%$ matte Sn | MSL1 $^{[2]}$ | $\underline{\text { H406 }}$ |

［1］Max peak reflow temperature of $235^{\circ} \mathrm{C}$
［2］Max peak reflow temperature of $260^{\circ} \mathrm{C}$
［3］4－Digit lot number XXXX

## 

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## Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
| :---: | :---: | :---: | :---: |
| 1 | Vpd | Power Control Pin. For maximum power, this pin should be connected to 5 V . A higher voltage is not recommended. For lower idle current, this voltage can be reduced. |  |
| 2, 4, 7 | GND | Ground: Backside of package has exposed metal ground slug that must be connected to ground thru a short path. <br> Vias under the device are required. | $\frac{\text { OGND }}{=}$ |
| 3 | RFIN | This pin is AC coupled and matched to 50 Ohms. | RFIN O-- |
| 5, 6 | RFOUT | RF output and bias for the output stage. The power supply for the output device needs to be supplied to these pins. |  |
| 8 | Vcc | Power supply voltage for the first amplifier stage. An external bypass capacitor of 330 pF is required. This capacitor should be placed as close to the devices as possible. |  |

## Application Circuit



Note 1: C3 should be located < 0.020" from Pin 8 (Vcc)
Note 2: C2 should be located $<0.020$ " from L1.

|  | TL1 | TL2 | TL3 |
| :---: | :---: | :---: | :---: |
| Impedance | 50 Ohm | 50 Ohm | 50 Ohm |
| Length | $0.038 "$ | $0.231 "$ | $0.1 "$ |

## Evaluation PCB

List of Materials for Evaluation PCB $104989{ }^{[1]}$

| Item | Description |
| :--- | :--- |
| J1－J2 | PCB Mount SMA RF Connector |
| J3 | 2 mm DC Header |
| C1－C3 | 330 pF Capacitor， 0603 Pkg． |
| C4 | $2.2 \mu$ F Capacitor，Tantalum |
| C5 | 0.6 pF Capacitor， 0603 Pkg． |
| C6 | 1.6 pF Capacitor，0603 Pkg． |
| C7 | 100 pF Capacitor， 0603 Pkg． |
| L1 | 3.9 nH Inductor，0603 Pkg． |
| U1 | HMC406MS8G（E）Amplifier |
| PCB［2］ | 105021 Eval Board |

［1］Reference this number when ordering complete evaluation PCB
［2］Circuit Board Material：Roger 4350
The circuit board used in the application should use RF circuit design techniques．Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be con－ nected directly to the ground plane similar to that shown．A sufficient number of via holes should be used to connect the top and bottom ground planes． The evaluation board should be mounted to an appropriate heat sink．The evaluation circuit board shown is available from Hittite upon request．

